

TOSHIBA FIELD EFFECT TRANSISTOR SILICON N CHANNEL MOS TYPE

# 2SK2162

AUDIO FREQUENCY POWER AMPLIFIER APPLICATION

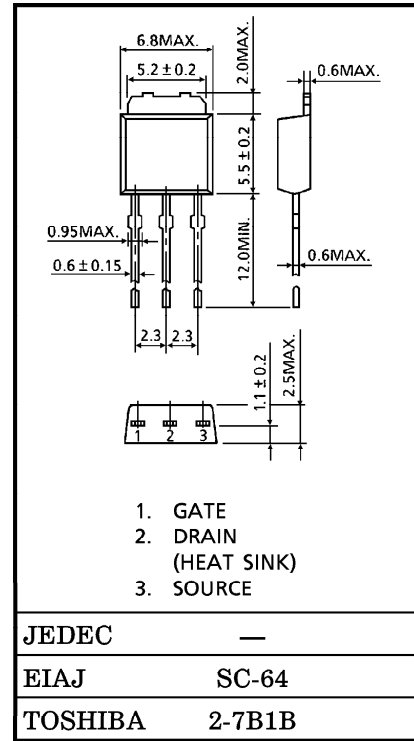
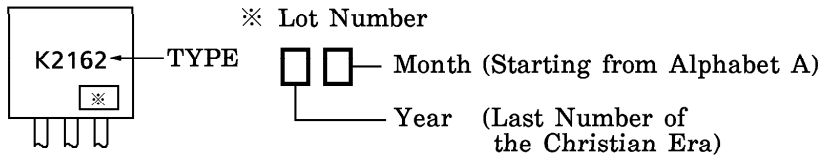
INDUSTRIAL APPLICATIONS  
Unit in mm

- High Breakdown Voltage :  $V_{DSS}=180V$
- High Forward Transfer Admittance :  $|Y_{fs}|=0.7S$  (Typ.)
- Complementary to 2SJ338

MAXIMUM RATINGS ( $T_a = 25^\circ C$ )

| CHARACTERISTIC                           | SYMBOL    | RATING   | UNIT       |
|--|-----------|----------|------------|
| Drain-Source Voltage                     | $V_{DSS}$ | 180      | V          |
| Gate-Source Voltage                      | $V_{GSS}$ | $\pm 20$ | V          |
| Drain Current                            | $I_D$     | 1        | A          |
| Power Dissipation ( $T_c = 25^\circ C$ ) | $P_D$     | 20       | W          |
| Channel Temperature                      | $T_{ch}$  | 150      | $^\circ C$ |
| Storage Temperature Range                | $T_{stg}$ | -55~150  | $^\circ C$ |

MARKING



Weight : 0.36g

ELECTRICAL CHARACTERISTICS ( $T_a = 25^\circ C$ )

| CHARACTERISTIC                  | SYMBOL        | TEST CONDITION                  | MIN. | TYP. | MAX.      | UNIT    |
|---------------------------------|---------------|---------------------------------|------|------|-----------|---------|
| Gate Leakage Current            | $I_{GSS}$     | $V_{DS}=0, V_{GS}=\pm 20V$      | —    | —    | $\pm 100$ | $\mu A$ |
| Drain-Source Breakdown Voltage  | $V_{(BR)DSS}$ | $I_D=10mA, V_{GS}=0V$           | 180  | —    | —         | V       |
| Gate-Source Cut-off Current     | $V_{GS(OFF)}$ | $V_{DS}=10V, I_D=10mA$          | 1.4  | —    | 2.8       | V       |
| Drain-Source Saturation Voltage | $V_{DS(ON)}$  | $I_D=0.6A, V_{GS}=10V$          | —    | 1.7  | 3.0       | V       |
| Forward Transfer Admittance     | $ Y_{fs} $    | $V_{DS}=10V, I_D=0.3A$          | —    | 0.7  | —         | S       |
| Input Capacitance               | $C_{iss}$     | $V_{DS}=10V, V_{GS}=10, f=1MHz$ | —    | 170  | —         | pF      |
| Output Capacitance              | $C_{oss}$     |                                 | —    | 45   | —         | pF      |
| Reverse Transfer Capacitance    | $C_{rss}$     |                                 | —    | 17   | —         | pF      |

**This transistor is the electrostatic sensitive device.  
Please handle with caution.**

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